AMENDMENTS TO THE CLIAMS

Claim 1 (original): A semiconductor laser comprising:

a substrate;

a semiconductor lamination portion including an active layer laminated on the substrate, the semiconductor lamination portion being made of a material having a cleavage plane not parallel to a cleavage plane of the substrate; and

a metal layer portion provided between the substrate and the active layer in a vicinity of a resonance cavity end face.

Claim 2 (original): The semiconductor laser according to claim 1, wherein the metal layer portion includes an element which is contained in the semiconductor lamination portion.

Claim 3 (original): The semiconductor laser according to claim 1, wherein the metal layer portion is formed so as to have a width which is wider than that of a stripe-shaped portion for emitting and narrower than that of a semiconductor chip.

Claim 4 (original): The semiconductor laser according to claim 1, wherein the metal layer portion is formed on a part of the semiconductor lamination portion contacted with the substrate.

Claim 5 (original): A method for manufacturing a semiconductor laser comprising the steps of:

forming a semiconductor lamination portion including an active layer on a substrate, the semiconductor lamination portion being made of the material having a cleavage plane not parallel to a cleavage plane of the substrate,

forming a metal layer portion by melting a part of the semiconductor lamination portion; and

forming resonance cavity end faces by cleaving the semiconductor lamination portion at the metal layer portion.

Claim 6 (original): The method for manufacturing the semiconductor laser according to claim 5, wherein the process of forming the metal layer portion is performed by irradiating a laser beam from a back surface of the substrate opposite to a surface laminated with the semiconductor lamination portion, and thereby melting a part of the semiconductor lamination portion.

Claim 7 (currently amended): The method for manufacturing the semiconductor laser according to claim ~~5~~ 6, wherein a wavelength of the laser beam is set longer than a wavelength corresponding to a band gap of the active layer and shorter than a wavelength corresponding to a band gap of a semiconductor layer to be melted.